



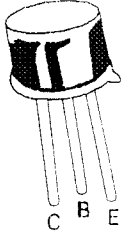
SOLID STATE INC.

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SILICON POWER SWITCHING TRANSISTORS

2N5320, 2N5321 NPN
2N5322, 2N5323 PNP



TO-39
Metal Can Package

Medium Power Amplifier and Switching Applications

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	2N5320	2N5321	2N5322	2N5323	UNITS
Collector Emitter Voltage	V_{CEO}	75	50	75	50	V
Collector Base Voltage	V_{CBO}	100	75	100	75	V
Emitter Base Voltage	V_{EBO}	7	5	7	5	V
Collector Current - Continuous	I_C	2.0				A
Base Current	I_B	1.0				A
Power Dissipation@ $T_a=25^\circ\text{C}$ Derate Above 25°C	P_D	1 5.71				W mW/ $^\circ\text{C}$
Power Dissipation@ $T_c=25^\circ\text{C}$ Derate Above 25°C	P_D	10 57.14				W mW/ $^\circ\text{C}$
Operating And Storage Junction Temperature Range	T_j, T_{slg}	- 65 to +200				$^\circ\text{C}$

THERMAL CHARACTERISTICS

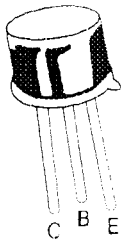
Junction to Ambient in free air	$R_{th(j-a)}$	175	$^\circ\text{C/W}$
Junction to Case	$R_{th(j-c)}$	17.5	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNITS
Collector Emitter Voltage	V_{CEO}	$I_C=100\text{mA}, I_B=0$ 2N5320/5322 2N5321/5323	75 50		V V
Collector Cut Off Current	I_{CEX}	$V_{CE}=70\text{V}, V_{BE}=1.5\text{V}, T_c=150^\circ\text{C}$ 2N5320/5322		5	mA
		$V_{CE}=45\text{V}, V_{BE}=1.5\text{V}, T_c=150^\circ\text{C}$ 2N5321/5323		5	mA
		$V_{CE}=100\text{V}, V_{BE}=1.5\text{V}$ 2N5320/5322		100	μA
		$V_{CE}=75\text{V}, V_{BE}=1.5\text{V}$ 2N5321/5323		100	μA
Emitter Cut Off Current	I_{EBO}	$V_{BE}=5\text{V}, I_C=0$ 2N5321/5323		100	μA
		$V_{BE}=7\text{V}, I_C=0$ 2N5320/5322		100	μA

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TO-18
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ELECTRICAL CHARACTERISTICS (T_a=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
DC Current Gain	*h _{FE}	I _C =1A, V _{CE} =2V 2N5320/5322 *	10			
		I _C =0.5A, V _{CE} =4V 2N5320/5322 2N5321/5323	30 40		130 250	
Collector Emitter Saturation Voltage	*V _{CE (sat)}	I _C =500mA, I _B =50mA 2N5320 2N5321 2N5322 2N5323			0.5 0.8 0.7 1.2	V V V V
Base Emitter On Voltage	*V _{BE (on)}	I _C =500mA, V _{CE} =4V 2N5320/5322 2N5321/5323			1.1 1.4	V V

DYNAMIC CHARACTERISTICS

Small Signal Current Gain	h _{fe}	I _C =50mA, V _{CE} =4V, f=10MHz	5			
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SWITCHING CHARACTERISTICS

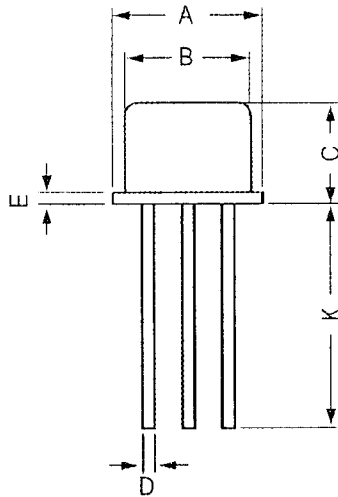
Turn On time	t _{on}	V _{CC} =30V, I _C =500mA, I _{B1} =50mA 2N5320/5321 2N5322/5323			80 100	ns ns
Turn Off time	t _{off}	V _{CC} =30V, I _C =500mA, I _{B1} =I _{B2} =50mA 2N5320/5321 2N5322/5323			800 1000	ns ns

*Pulsed: Pulse width ≤300μs, duty cycle ≤2%

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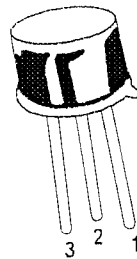
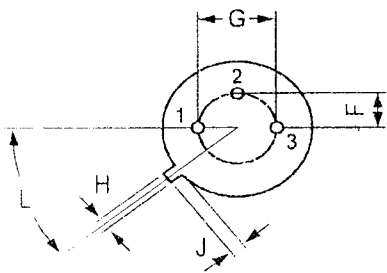
TO-39
 Metal Can Package

TO-39 Metal Can Package



All dimensions are in mm

DIM	MIN	MAX
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	—	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	—
L	42 DEG	48 DEG



PIN CONFIGURATION
 1. EMITTER
 2. BASE
 3. COLLECTOR